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Wavelength-extended photovoltaic infrared photodetectors


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We report the incorporation of a long-wavelength photovoltaic response (up to 8 μm) in a short-wavelength p-type GaAs heterojunction detector (with the activation energy of $E_A \sim 0.40$ eV), operating at 80 K. This wavelength-extended photovoltaic response is enabled by employing a non-symmetrical band alignment. The specific detectivity at 5 μm is obtained to be $3.5 \times 10^{12}$ cm Hz$^{-1/2}$/W, an improvement by a factor of $10^3$ over the detector without the wavelength extension. © 2014 AIP Publishing LLC. [http://dx.doi.org/10.1063/1.4869958]

Photovoltaic detectors are attractive for achieving (i) extremely low noise, (ii) high impedance, and (iii) low power dissipation, compared to photoconductive detectors. Various device concepts based on p-n junctions, quantum well (QW), quantum dot (QD), type-II InAs/GaSb, and quantum cascade (QCD) structures have been explored to implement photovoltaic operation. A key feature of this Letter is to have a built-in potential to sweep photocarriers out of the active region without an external field. Schneider et al. reported a four-zone low-noise photovoltaic QW infrared photodetector (QWIP) with the preferable transport of carriers toward one direction. In a n-i-p type-II InAs/GaSb/AlSb detector, internal electric field associated with the junction as the built-in asymmetry. Recently, Barve and Krishna reported a photovoltaic QD infrared photodetector (QDIP) based on the QCD concept, in which directional transfer of carriers between QDs is favored by cascade transitions through phonon coupling.

In addition to optimizing optical performance of the active region, the detectivity ($D^*$) of a detector is mainly limited by the dark current in photoconductive mode, or $R_\sigma A$ (where $R_\sigma$: zero-bias differential resistance, $A$: active area) in photovoltaic mode, which is determined by the activation energy ($E_A$). A detector operating in the longer wavelength range requires a reduced $E_A$, which typically lowers the detectivity, as a consequence of the increased dark currents and detector noise. In this Letter, we report a detector capable of operating up to 8 μm in the photovoltaic mode, while having the $R_\sigma A$ value determined by $E_A = 0.40$ eV. This means that the $R_\sigma A$ value is significantly greater than a conventional 8-μm threshold detector (which has the activation energy of 0.155 eV). Improvement by a factor of $\sim 10^3$ in $D^*$ is thus expected from the $R_\sigma A$ improvement. Experimentally, $D^*$ of the 8-μm-threshold single-emitter detector reported here is $10^3$ times higher than that of a previously reported 30-period detector.

The detector architecture uses the standard structure of internal-photoemission detectors, in which a highly p-type doped GaAs acts as the photon absorber and emitter. Figure 1(a) shows the valence band, which has a non-symmetrical band configuration. In addition to an offset ($\delta E_i$) between the barriers below and above the emitter, one of the AlGaAs barriers is graded to further increase the non-symmetry, and facilitate the transport of photoexcited holes at zero bias. The room-temperature photovoltaic operation has been reported elsewhere. For comparison, different gradients of Al fractions [i.e., $x$ varies from 0.45 to 0.75, or remains a constant (Table I)] were investigated. Figure 1(b) schematically shows the inter-valence band (IVB) transitions mainly responsible for photon absorption and hole escape over the barrier (through internal photoemission). To determine $E_A$, the characteristics of dark current-voltage-temperature (I-V-T) were measured, as shown in Fig. 2(a). The characteristics of dark currents and $E_A$ are shown in Figs. 2(a) and 2(b). Figure 2(b) plots $R_\sigma A$ values extracted from I-V-T data, where a previous symmetrical GaAs/Al$_{0.5}$Ga$_{0.43}$As detector (sample SP3) is also shown for comparison. The Arrhenius plots are used to fit $R_\sigma A$ and determine $E_A$ to be 0.37, 0.40, and 0.49 eV for samples SP1005, SP1007, and SP1001 (Table I), respectively. Except for SP1001, the obtained $E_A$ values are comparable to the designed internal work function ($\Delta$) of $\sim 0.40$ eV, in accordance with the p-type GaAs/Al$_{0.75}$Ga$_{0.25}$As junction by taking into account p-type-doping effects. The $R_\sigma A$-$T$ characteristic giving $E_A \sim 0.4$ eV demonstrates that both SP1005 and SP1007 behave like a 3-μm threshold detector.

The photovoltaic responsivity and detectivity ($D^*$) at 80 K are shown in Figs. 3(a) and 3(b), respectively. Spectral

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FIG. 1. (a) The valence-band diagram of a graded (solid line)/flat (dashed line) barrier structure. Bidirectional photocurrents can simultaneously exist in the sample for photovoltaic operation, as shown by $I_x^+(+) \text{ and } I_x^-(−)$, corresponding to forward and reverse photocurrents, respectively. $x_1$, $x_2$, and $x_3$ are the Al fractions of the barriers as described in Table 1. $\delta E_i$ is an offset between the barriers below and above the emitter. (b) Schematic of optical transitions between two valence bands, i.e., the heavy-hole (HH) and light-hole (LH) bands. For holes to escape over a potential barrier, optical transitions typically occur with the assistance of phonons.
response was measured by a Perkin-Elmer system 2000 Fourier transform infrared spectrometer. The dimension of the sample is $400 \times 400 \, \mu m^2$ mesas, with an area of $260 \times 260 \, \mu m^2$ opened in the center allowing for front-side illumination. A bolometer with known sensitivity is used for background measurements and calibration of the responsivity. $D^*$ was obtained by using $D^* = R / (2pJ + 4kT/R_{diff}A)^{1/2}$, where $R$ is the responsivity, $J$ is the dark current density, and $R_{diff}$ is the differential resistance. At zero bias where the shot noise vanishes, this expression is reduced to the normal form in terms of the Johnson noise. $^4$ With decreasing temperature, $R_{diff}$ rapidly increases for the bias around 0 V. To calculate photovoltaic $D^*$ at 80 K, extrapolation of $R_0$ in terms of the Arrhenius plots [Fig. 2(b)] has been carried out.

An interesting feature in the spectral response of the graded-barrier samples is the large redshift in the threshold wavelength under photovoltaic operation (doubling the operating wavelength range). From the photoreponse characteristic point of view, the device with $E_A \sim 0.40 \, eV$ acts as an 8-μm threshold detector. Notice that the flat-barrier sample SP1001 does not respond beyond 3.9 μm, which is similar to the symmetrical GaAs/Al$_{0.57}$Ga$_{0.43}$As detector as observed before (sample SP3). $^{10}$ Another feature being observed is the zero-responsivity point lying between 3.4 and 3.5 μm, which is an indication of bidirectional photocurrents simultaneously existing in the sample [see Fig. 1(a)]. This can be understood since photoexcited holes in the emitter can emit over both sides of the barriers, which normally have the threshold wavelengths of 3 and 4 μm, corresponding to the heterointerfaces of GaAs/Al$_{0.57}$Ga$_{0.43}$As and GaAs/Al$_{0.57}$Ga$_{0.43}$As, respectively. The photocurrent cancellation leads to the occurrence of zero response between 3 and 4 μm. Several zero-response points taking place in sample SP1001 are related to its band alignment with a flat barrier.

In general, threshold redshifting mostly results from bias-related effects, such as image-force barrier lowering and quantum tunneling. However, these effects are absent in the photovoltaic operating mode. A testimony of our observations was justified as being due to the high-energy photon excitation. Since the bottom contact (BC), emitter and top contact (TC) are highly doped, photoexcited holes can be created in all of these layers. Because of the graded barrier, high-energy photons can give rise to a net flow of photoexcited holes from BC to emitter. Some of the photoexcited holes are captured by the emitter. These high-energy captured holes tend to increase the energies of holes $^{12}$ originally in the emitter, and excite them to high-energy states. As a consequence, the energies of photons needed in order to excite holes to escape over the barrier can be correspondingly reduced, giving rise to a long-wavelength response. This process takes place in the hole transport from BC to TC, in agreement with observed wavelength-extended response corresponding to the reverse photocurrents (Fig. 3).

To justify the above mechanism, spectral response has been measured with the use of different long-pass filters (with the cut-on wavelength of $\lambda_{CO}$) and different intensities of incoming light, as shown in Fig. 4. This varies the energy or the concentration of photoexcited holes injected into the emitter. By using a filter with $\lambda_{CO} = 3.60 \, \mu m$, the short-wavelength response [labeled region 1 of Fig. 3] should disappear, as the escape of holes from the emitter to the BC cannot be accomplished because of the missing of the $h\nu > 0.34 \, eV$ $(\lambda < 3.60 \, \mu m)$ photons. For the same reason, photoexcited holes in the BC will be unable to overcome the
graded barrier (highest barrier \( \sim 0.4 \text{ eV} \)) to enter into emitter. This suppresses the long-wavelength response as well [labeled region 2 of Fig. 3], according to the aforementioned energy-transfer mechanism. As expected [Fig. 4(a)], photovoltaic response was unseen throughout the entire spectral range. In contrast, the use of a filter with \( \lambda_{CO} = 2.40 \mu\text{m} \) gives rise to both short- and long-wavelength response owing to allowed emitter-to-BC and BC-to-emitter hole transport. The efficiency of energy transfer between photoexcited holes and holes in the emitter could be a critical factor determining the long-wavelength response. Such energy transfer results from carrier scatterings and could be subject to degradation from hole-impurity scattering as the emitter is highly doped. With increasing the concentration of photoexcited holes, enhanced hole-hole scatterings can be expected, leading to distinct response in long-wavelength range, as shown in Fig. 4(b). By calibrating the variation of the incoming light intensity, the short-wavelength portion of the response is expected to remain the same. However, the long-wavelength portion is almost negligible when the light intensity is reduced to 2.9%, and quickly rises up when the incoming light increases to 7.3%, where 100% of light corresponds to the default optical aperture in the experiment. This may also explain the response characteristic of sample SP1001 not beyond 3.9 \( \mu\text{m} \), where because of the flat-barrier configuration the net injection of photoexcited holes from the BC to emitter is negligible.

Higher activation energy of the dark current-voltage characteristics than the photoresponse threshold energy can provide a significant improvement of the detector performance. According to \( R_0A \sim \exp(-E_A/kT) \), the \( R_0A \) value (at 80 K) of our detector with \( E_A = 0.40 \text{ eV} \) (responding up to 8 \( \mu\text{m} \)) is nearly \( 10^{15} \) times higher than a conventional detector with \( E_A = 0.155 \text{ eV} \) (without wavelength extension, also responding up to 8 \( \mu\text{m} \)), which gives nearly \( 10^5 \) improvement in \( D^* \). To experimentally evaluate the \( D^* \) improvement factor, same type of internal-photoemission detectors was used, as shown in Fig. 3(b) (this detector contains 30 periods of emitters and barriers), which is nearly \( 10^5 \) times less than the present detector.

There are two main reasons causing the relatively low responsivity and thus low quantum efficiency (QE) in the present detector: the absorption of the emitter and lifetime of holes. The single-emitter structure only gives \( \sim 2\% \) absorption efficiency, and thus can be improved at least by a factor of 10 using multiple periods. The fast carrier relaxation time \( \sim 0.1 \text{ ps} \) in \( 1 \times 10^{19} \text{ cm}^{-3} \) p-type doped GaAs is another

![FIG. 4. (a) Photovoltaic response measured by using different long-pass filters (\( \lambda_{CO} \) is the cut-on wavelength). A filter with \( \lambda_{CO} = 3.60 \mu\text{m} \) blocks the transport of photoexcited holes overcoming the graded-barrier region, thus suppressing both the short and long-wavelength response. (b) Variation of photovoltaic response with the intensities of incident light (through adjusting the optical aperture size of the spectrometer), where 100% of light corresponds to the default aperture size. The calibration of responsivity takes into account the variation of light, which leads to nearly unchanged responsivity values for the 3 \( \mu\text{m} \) wavelength range. The \( >3.5 \mu\text{m} \) response becomes almost negligible when the intensity of incoming light is reduced to 2.9%.](image-url)
reason of low QE, which can be possibly improved by a factor of $10^3 \text{--} 10^8$, by using quantum structures such as dots-in-well, which has the carrier lifetime in the nanosecond range. Although demonstrated in heterojunction detectors, the wavelength-extension idea is based on the non-symmetrical band alignment and thus can be applied to detectors consisting of quantum structures. To conclude, the present study demonstrated a wavelength-extended photovoltaic detector with a significantly high $R_0/A$ value. This offers a possibility of incorporating long-wavelength response into a short-wavelength detector with the advantage of low dark-current operation.

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